

Fig. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 20, a base layer 21, and various patterned layers 22-28. A central region 30 contains a series of rectangular structures 34, 35, and 36. A top layer 40 is patterned with rectangular structures 41, 42, and 43. A topmost layer 44 is also patterned. A dashed line A-A indicates a cross-section. Dimensions L1 and L2 are shown. A scale bar F is provided.

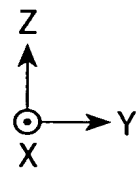


FIG. 2

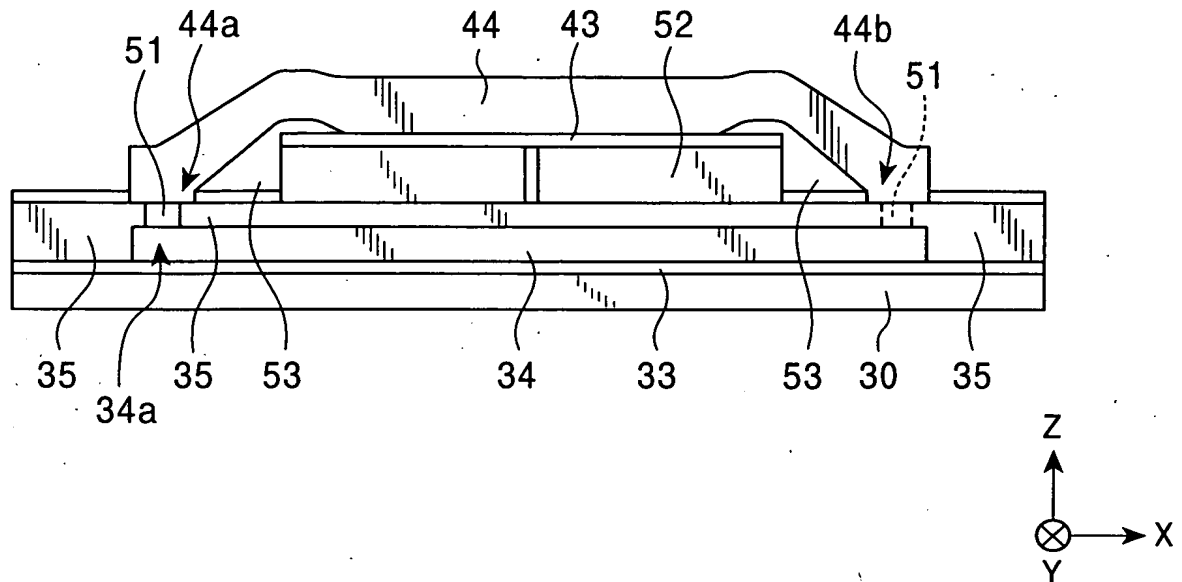
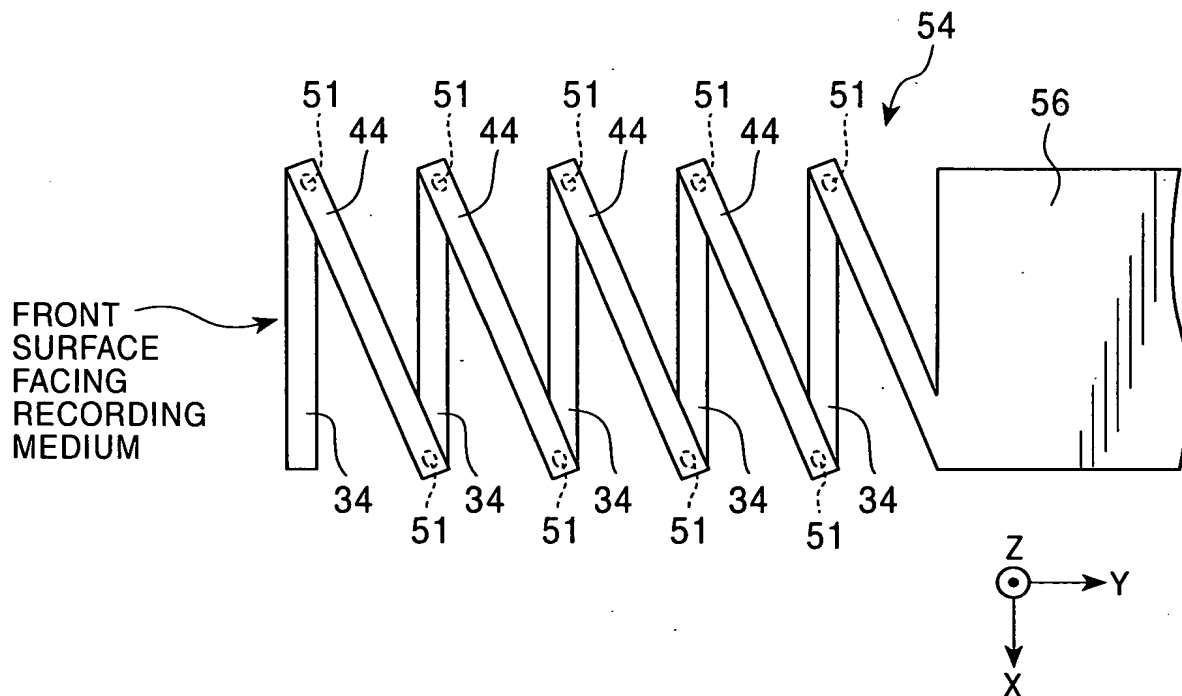


FIG. 3



[illegible]

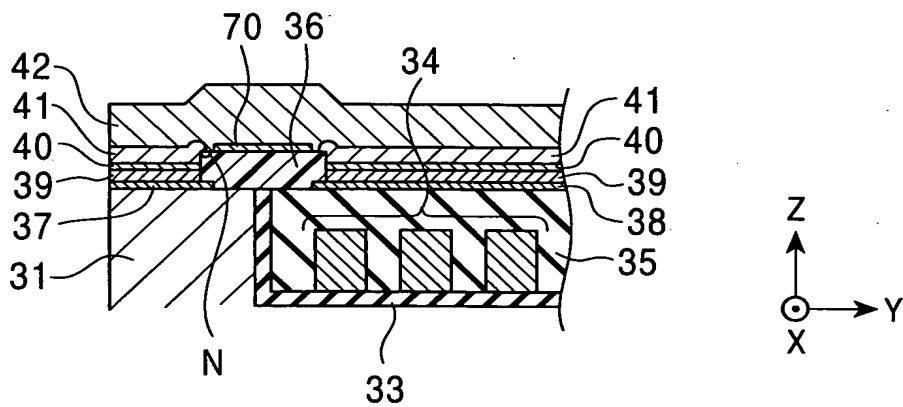


FIG. 7  
PRIOR ART

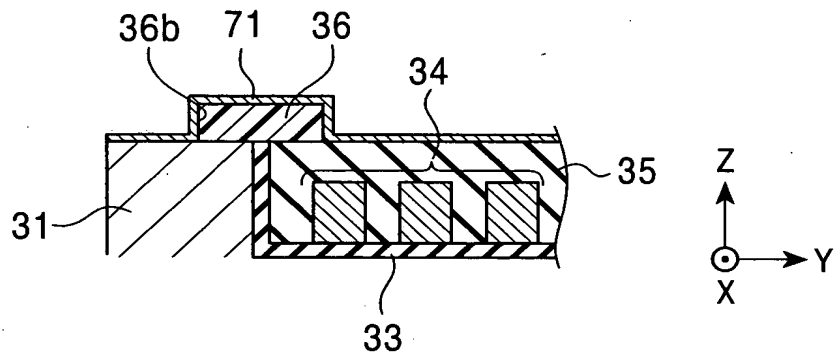


FIG. 8  
PRIOR ART

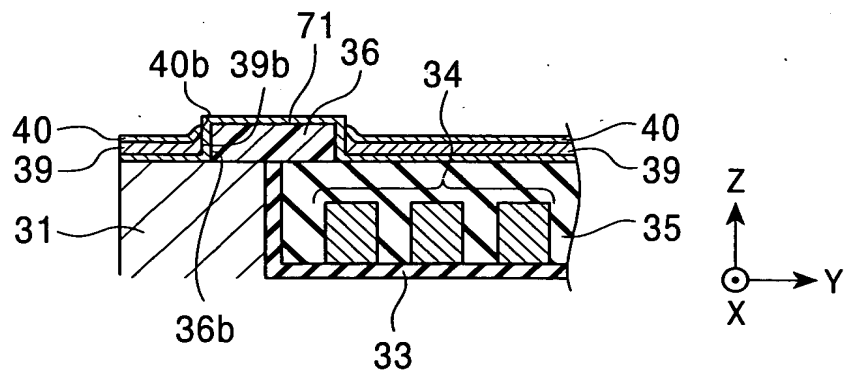
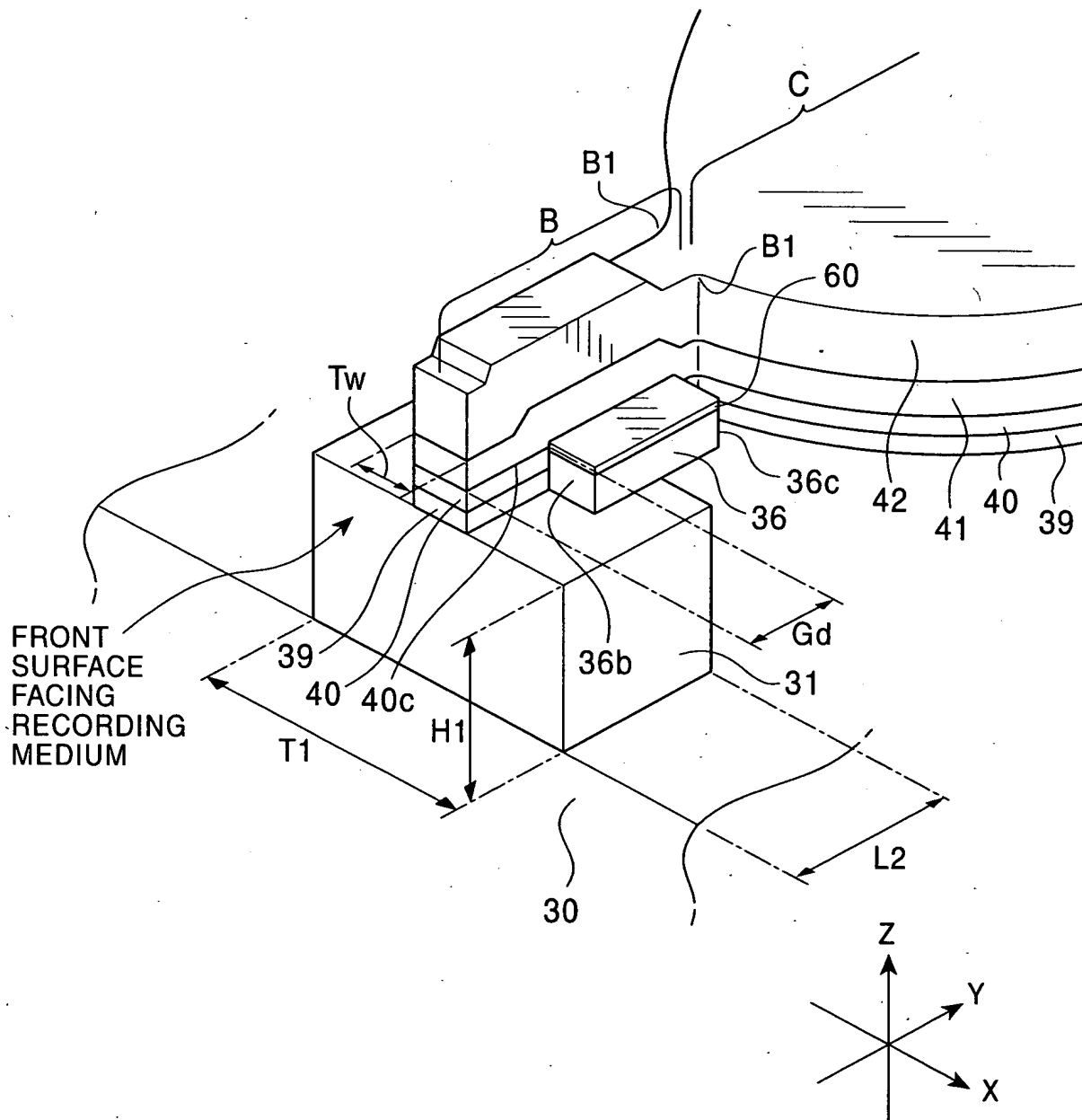


FIG. 9



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FIG. 10

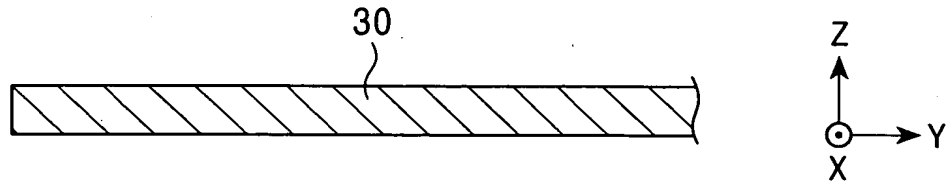


FIG. 11

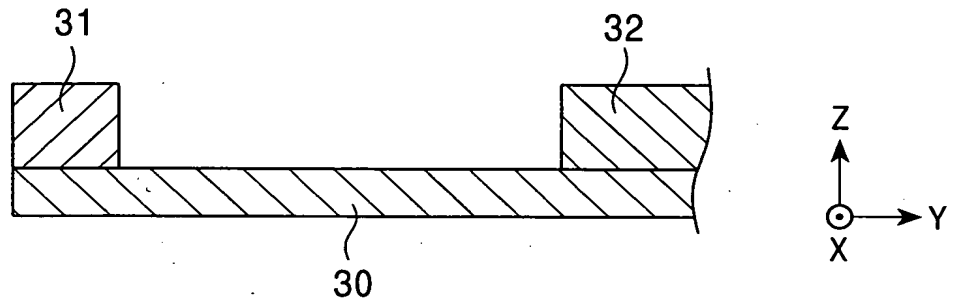


FIG. 12

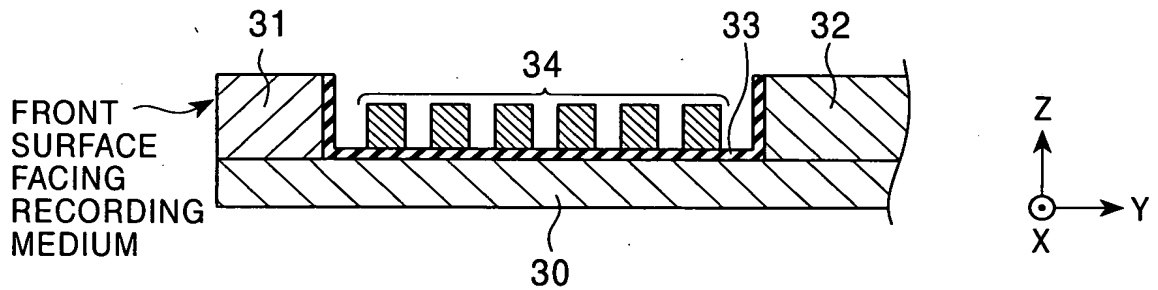
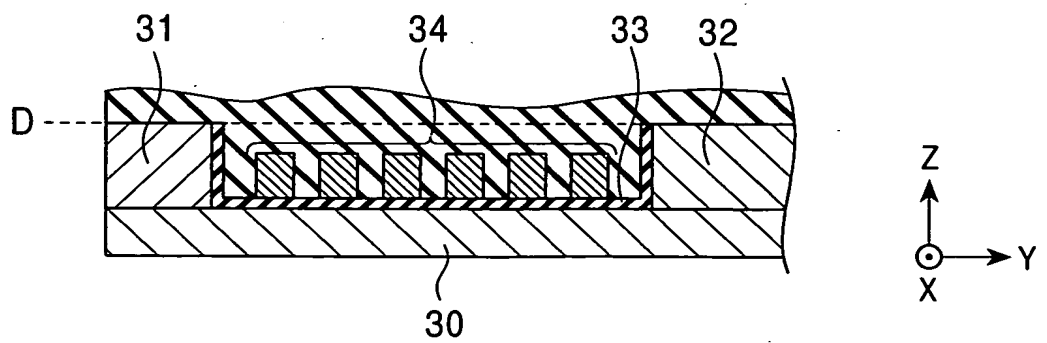


FIG. 13



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FIG. 14

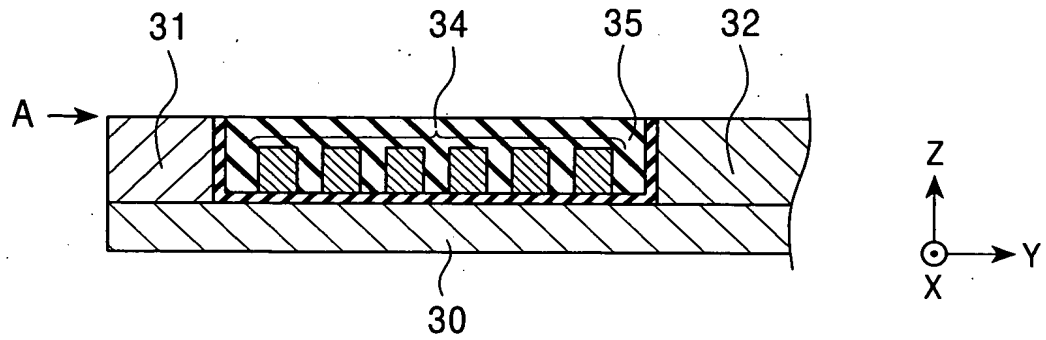


FIG. 15

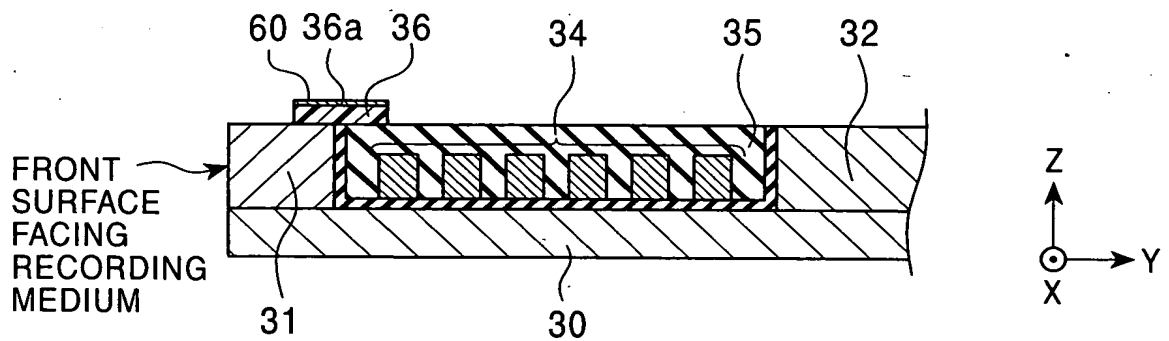


FIG. 16

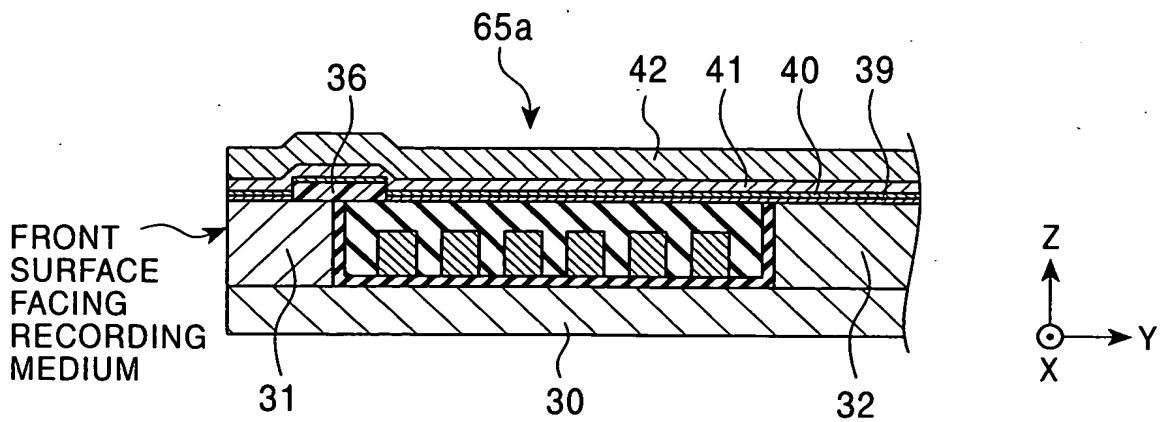




FIG. 17

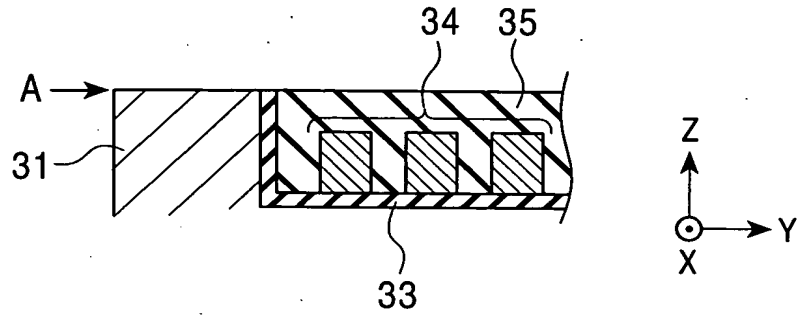


FIG. 18

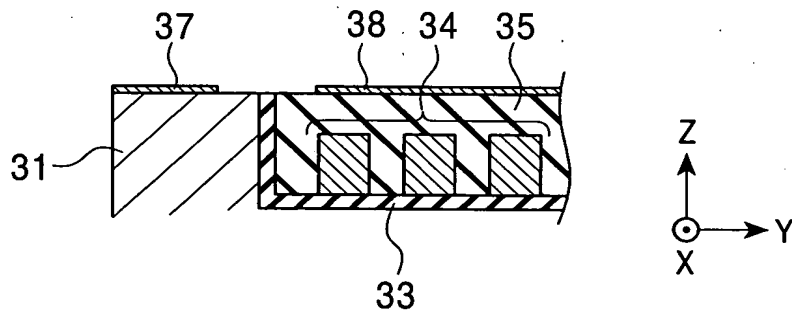
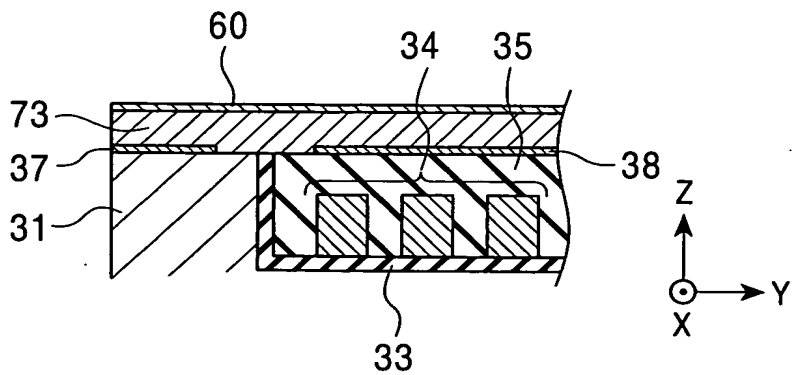


FIG. 19



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FIG. 20

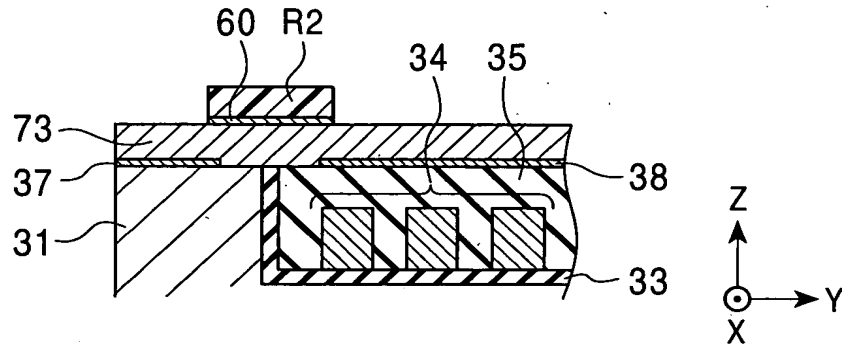


FIG. 21

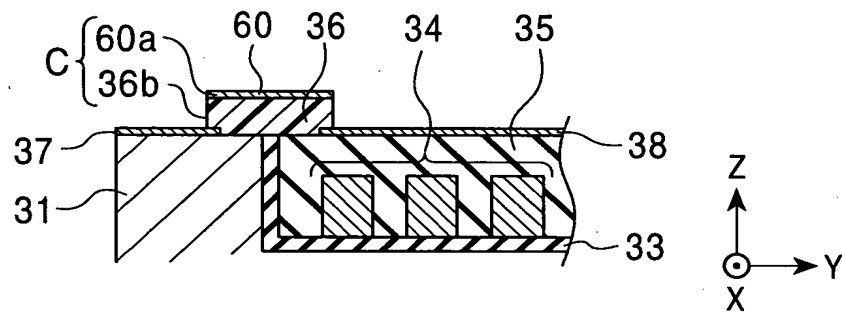
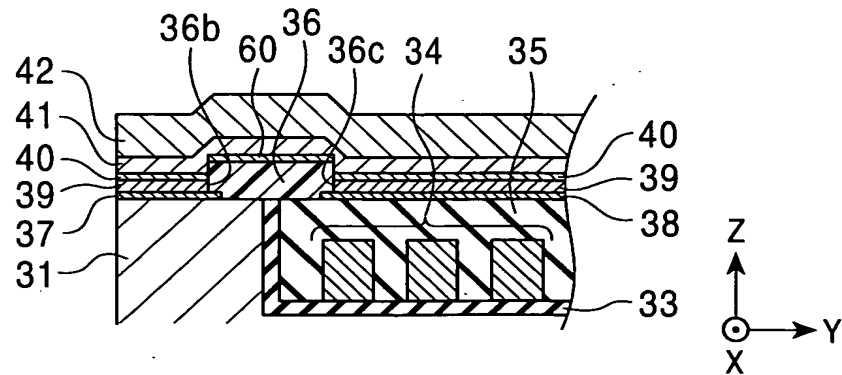
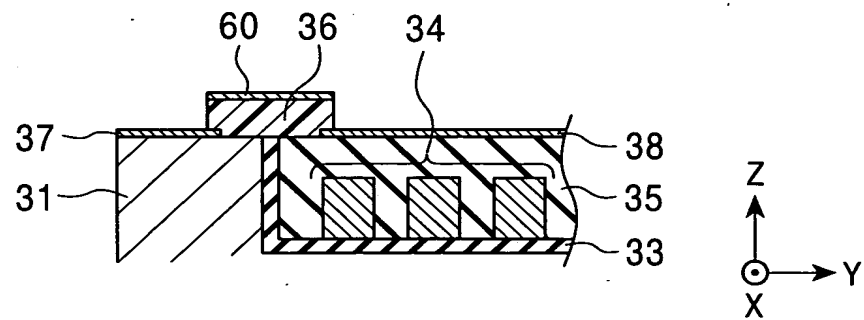


FIG. 22





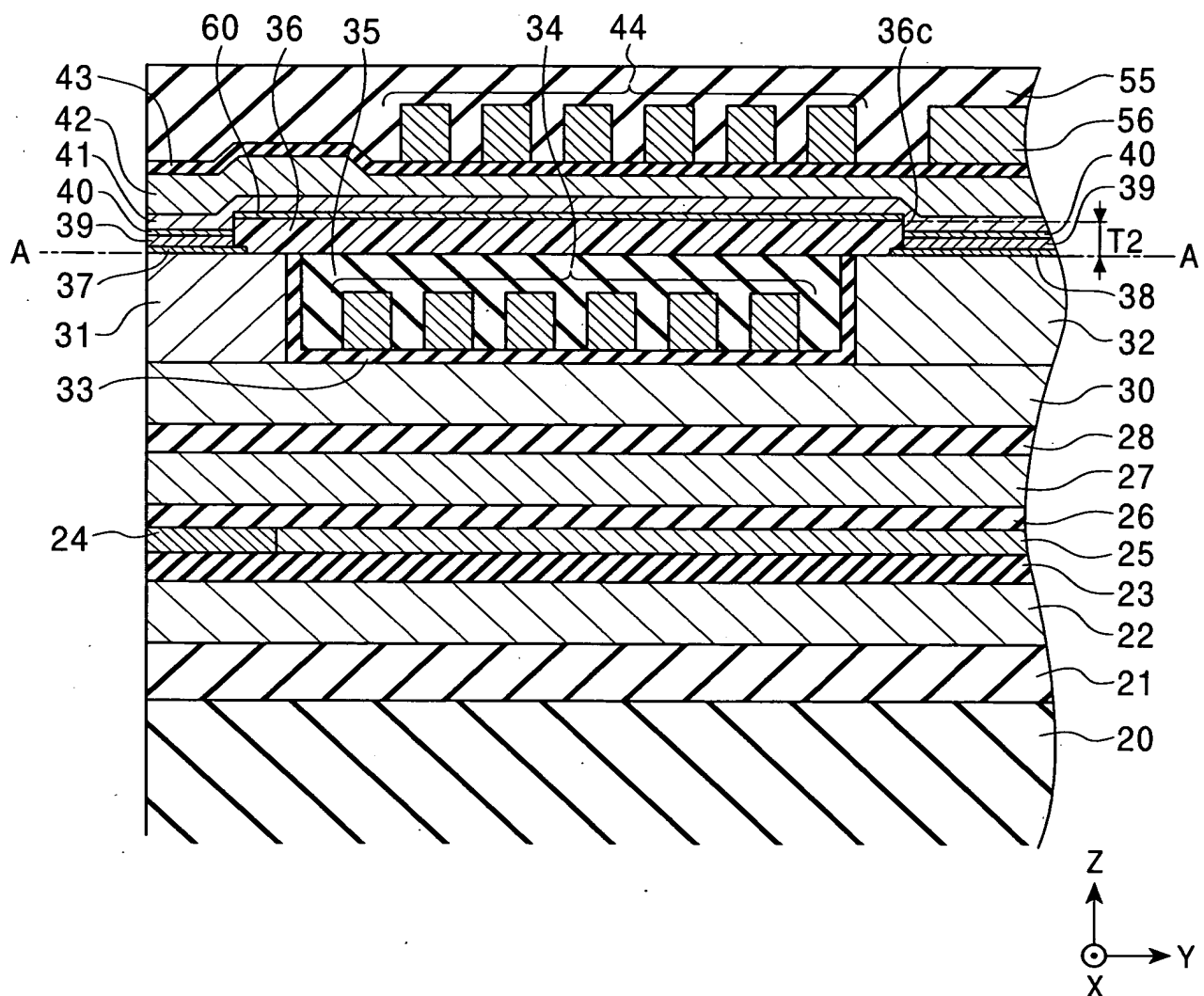
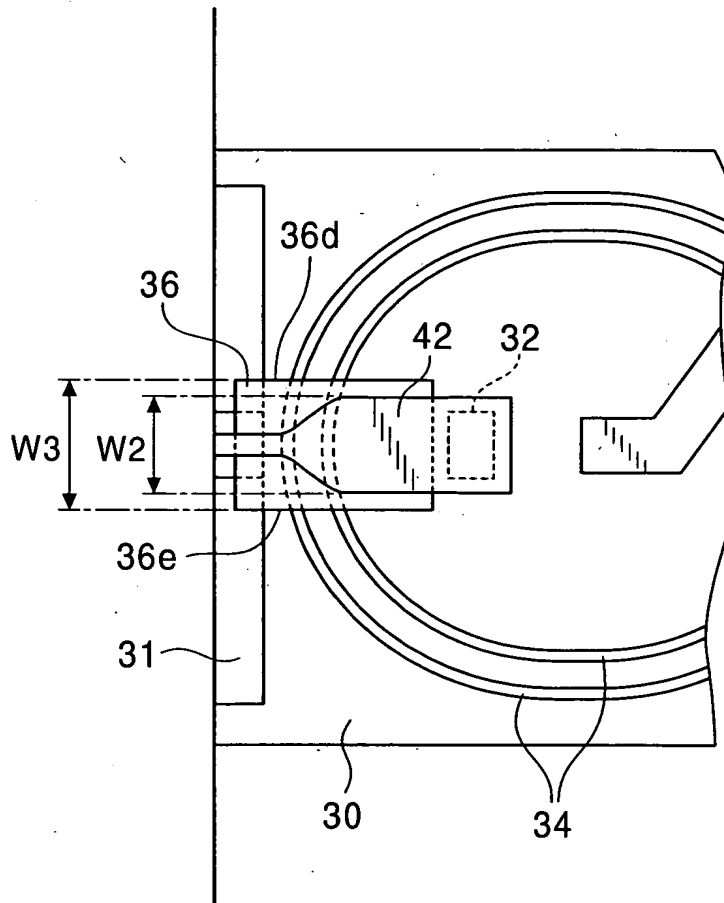


FIG. 26



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FIG. 27

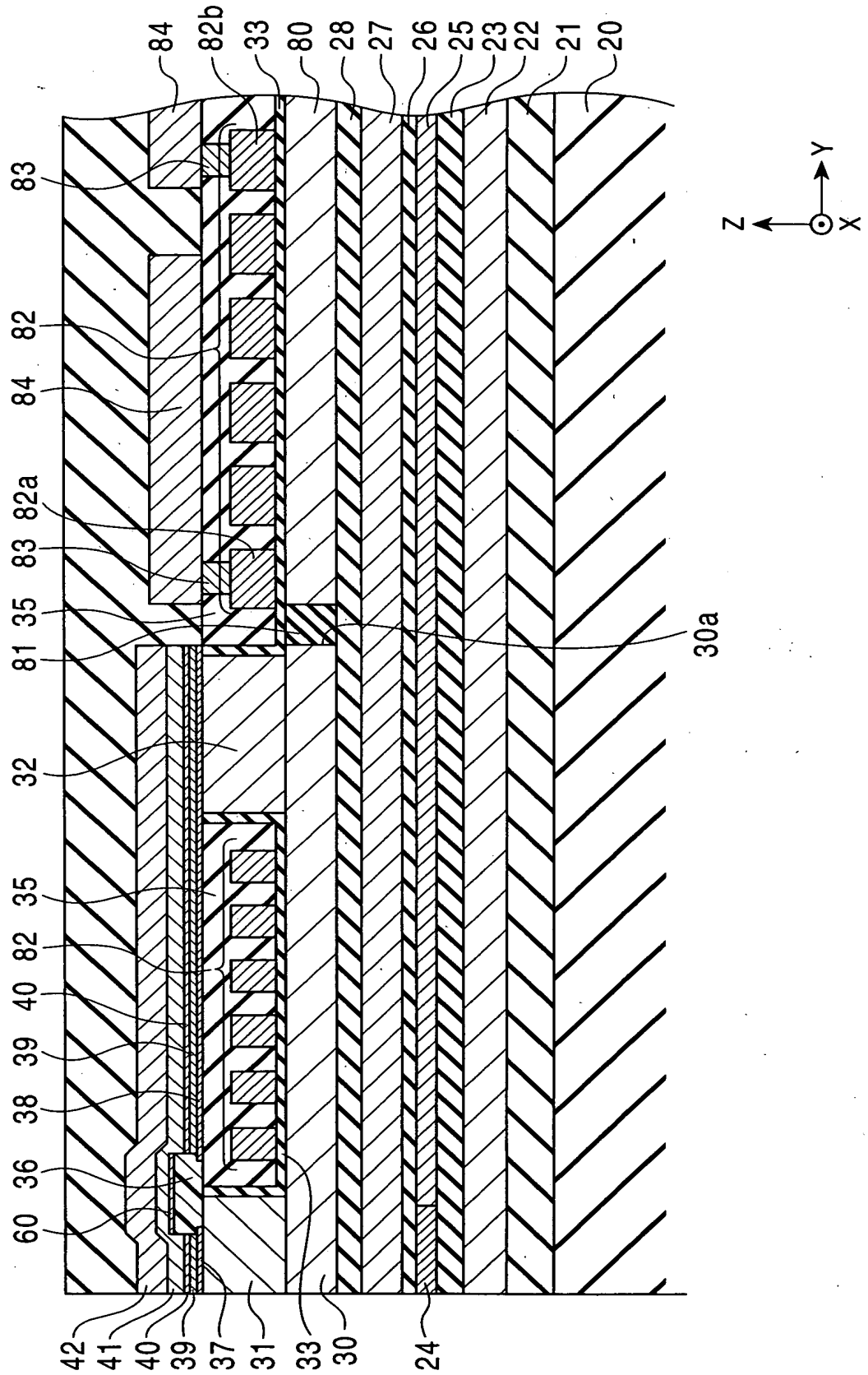


FIG. 28  
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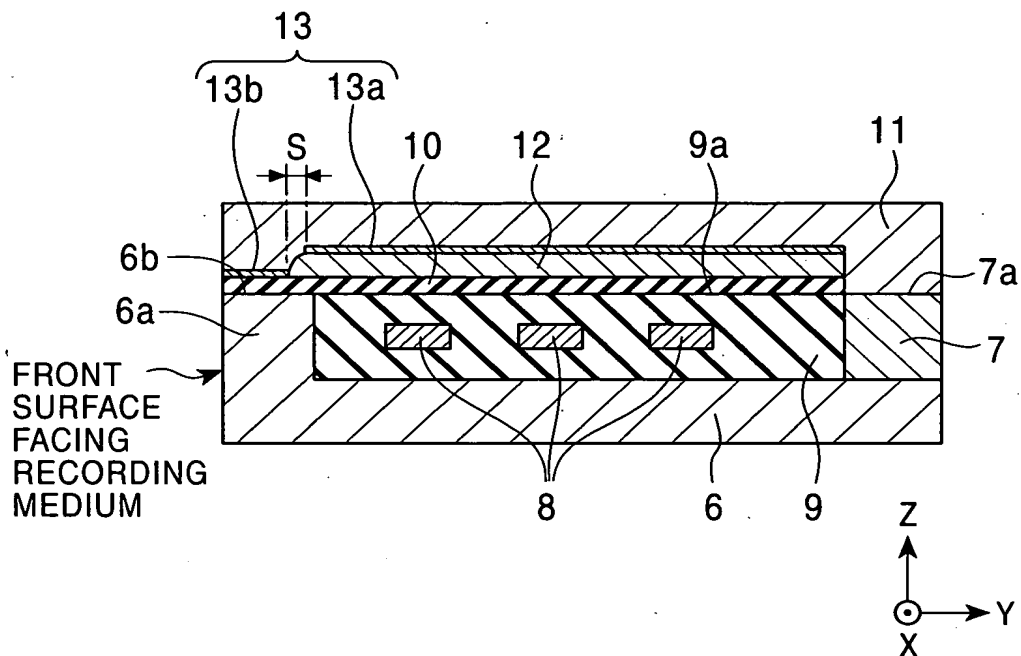


FIG. 29  
PRIOR ART

